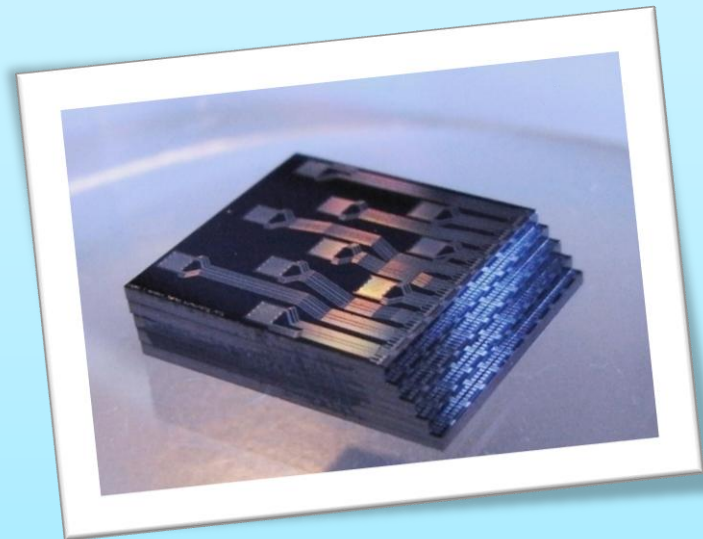


Electrical Characterization of Cu TSVs with Low Temperature Cu/Sn-BCB Hybrid Bonding



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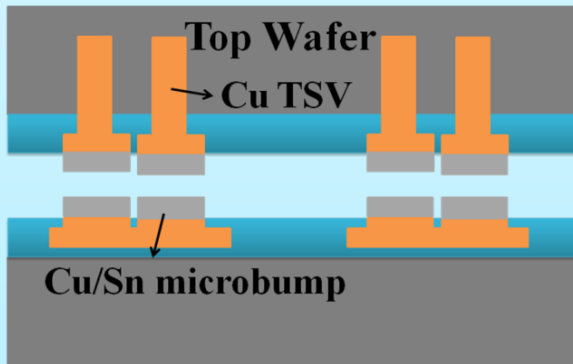
陳冠能 教授

I . Introduction

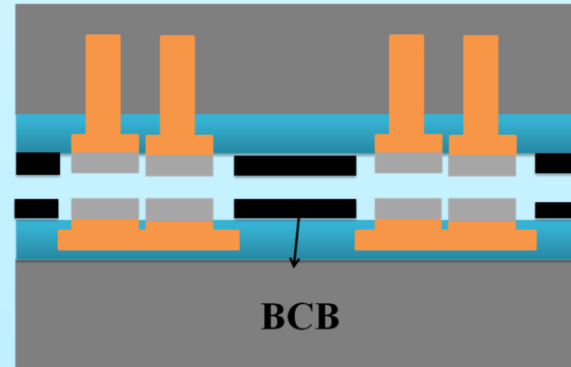
A wafer-level 3D integration structure with Cu TSVs based on Cu/Sn/Cu eutectic bonding and BCB hybrid bonding is demonstrated.

Kelvin structure and daisy chain design are adopted for electrical characterization and reliability evaluation.

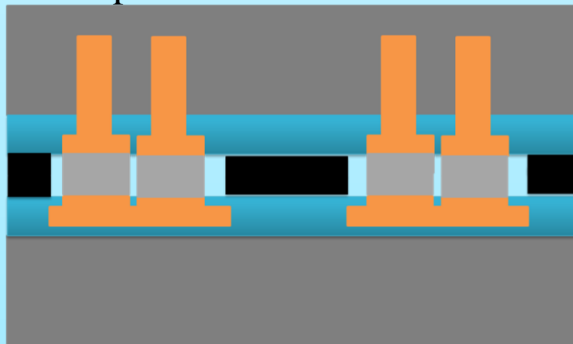
II . Process Flow and Integration Scheme



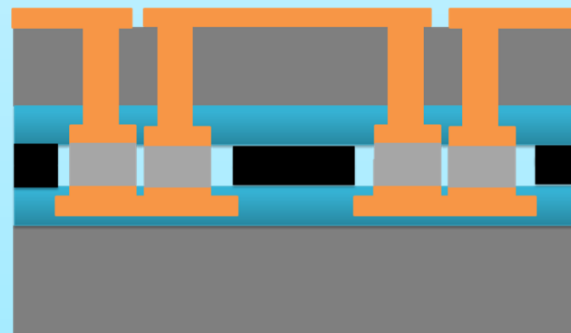
(a) Cu/Sn microbump scheme on the top and bottom wafer



(b) BCB spin coating and lithography



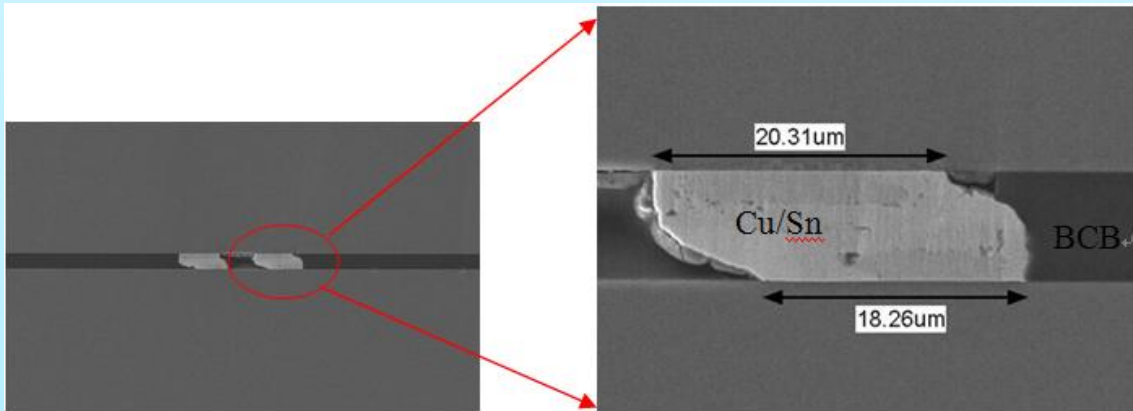
(c) Cu/Sn and BCB hybrid bonding



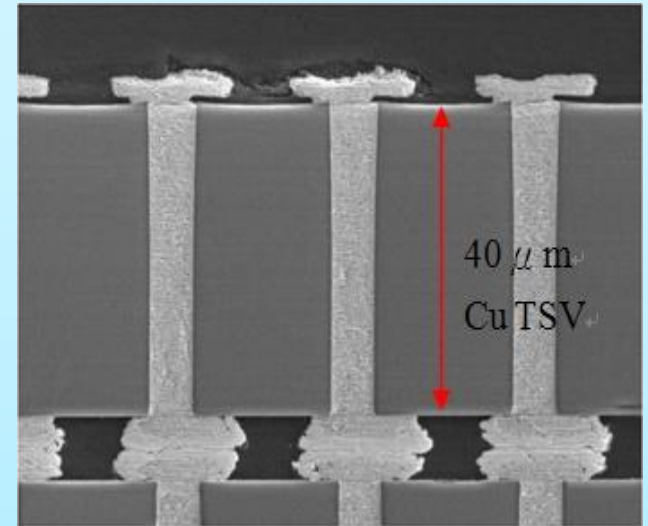
(d) Wafer thinning and backside metallization

◆ Demonstration of Cu/Sn & BCB Hybrid Bonding

- No interface exists at BCB-BCB bonding surface
- Thickness control of Sn → no Kirkendall voids

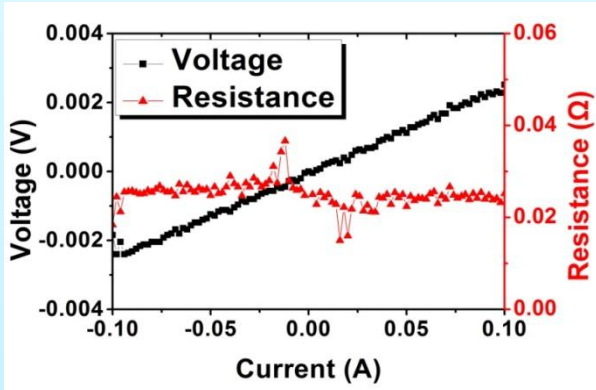


(a) SEM image

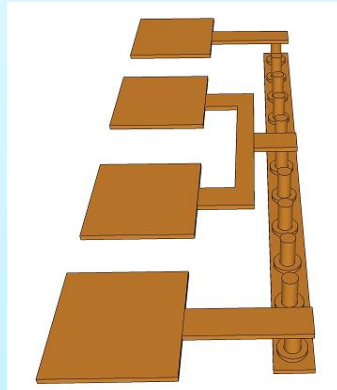


(b) SEM image of Cu TSVs

III. Electrical Characteristics of Cu TSV with Hybrid Bonding



(a) V-I & R- I curves



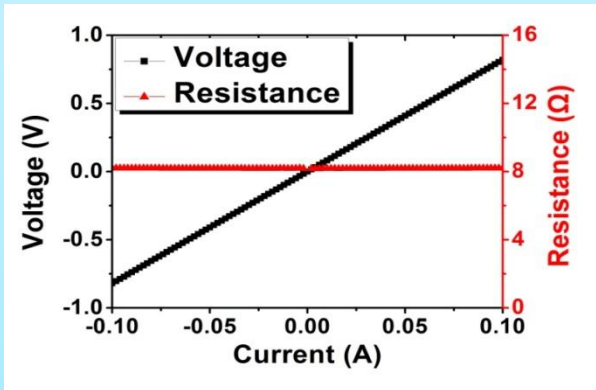
(b) Kelvin structure design

$$R_{kelvin} = R_{10\mu m TSV} + R_{Cu/Sn microbump}$$

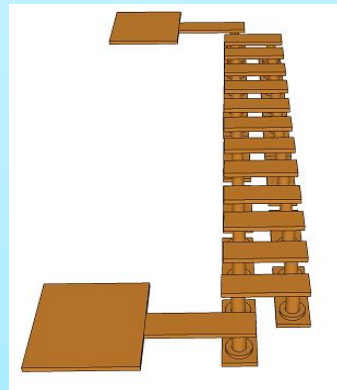
➤ Kelvin structure = single TSV + micro-joint structure

➤ Daisy chain → evaluate bonding integrity & integration performance

➤ 70%↑ of $R_{daisy chain}$ is contributed by $N \cdot R_s$, connected interface, bonding structure



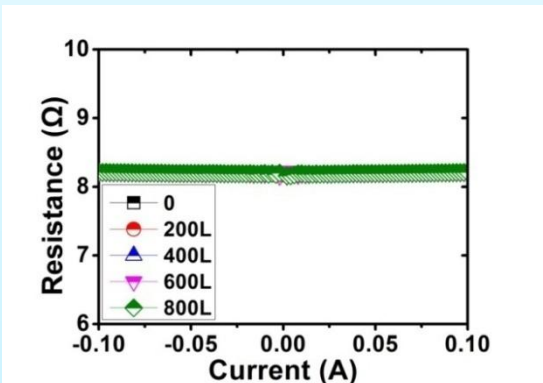
(c) V-I & R- I curves



(d) Daisy chain design with N=100 via chains

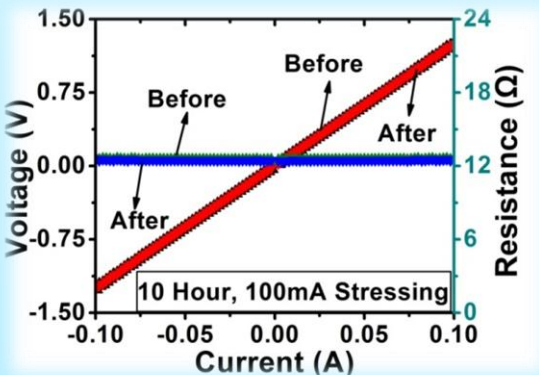
$$R_{daisy chain} = N \cdot (R_{Cu TSV} + R_{Cu/Sn microbump} + R_s)$$

IV. Reliability of Electrical Stressing and Humidity Test



(a) Multiple current stressing

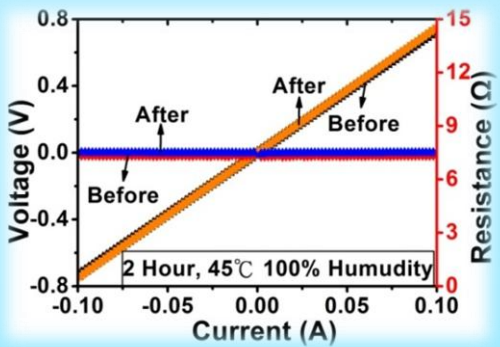
- Multiple current stressing(N=100) → excellent stability even after 800 cycles stressing
- Constant current stressing(N=150) → no obvious deterioration after 10 hrs stressing



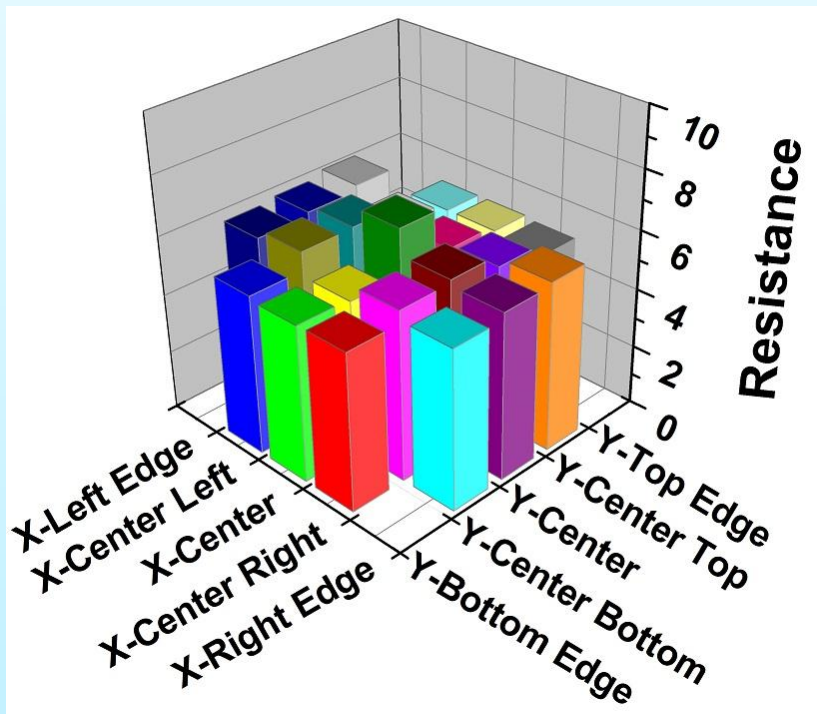
(b) 10hrs constant current stressing

- Humidity test → no apparent perturbation

➤ This 3D integration scheme possesses excellent reliability & electrical stability.



(c) 2hrs, 45°C & 100% humidity test



Characteristics of total resistances of N=50 via chains and locations on wafer

➤ Small deviation → good uniformity & integration performance

V. Conclusion

The advantage of Cu/Sn/Cu eutectic bonding and BCB hybrid bonding includes low bonding temperature and strong bonding strength.

Kelvin structure and daisy chain design are adopted for electrical characterization and reliability evaluation including *multiple current stressing*, *constant current stressing* and *humidity test*. The results indicate the developed 3D integration has excellent reliability and electrical stability, which is of great use to future applications.